Younghee Lee

List of Publications by Year
in descending order

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23 papers	1,317 citations	20 h-index	22 g-index
25 all docs	25 docs citations	25 times ranked	1221 citing authors

361296

677027

#	Article	IF	Citations
1	Atomic Layer Etching of Al₂O₃ Using Sequential, Self-Limiting Thermal Reactions with Sn(acac)₂ and Hydrogen Fluoride. ACS Nano, 2015, 9, 2061-2070.	7.3	131
2	Prospects for Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. ACS Nano, 2016, 10, 4889-4894.	7.3	120
3	Surface-Coating Regulated Lithiation Kinetics and Degradation in Silicon Nanowires for Lithium Ion Battery. ACS Nano, 2015, 9, 5559-5566.	7.3	118
4	Atomic Layer Etching of HfO₂Using Sequential, Self-Limiting Thermal Reactions with Sn(acac)₂and HF. ECS Journal of Solid State Science and Technology, 2015, 4, N5013-N5022.	0.9	85
5	Trimethylaluminum as the Metal Precursor for the Atomic Layer Etching of Al₂O₃ Using Sequential, Self-Limiting Thermal Reactions. Chemistry of Materials, 2016, 28, 2994-3003.	3.2	83
6	Selectivity in Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. Chemistry of Materials, 2016, 28, 7657-7665.	3.2	80
7	Thermal Atomic Layer Etching of Titanium Nitride Using Sequential, Self-Limiting Reactions: Oxidation to TiO₂ and Fluorination to Volatile TiF₄. Chemistry of Materials, 2017, 29, 8202-8210.	3.2	71
8	Coating Solution for High-Voltage Cathode: AlF₃ Atomic Layer Deposition for Freestanding LiCoO₂ Electrodes with High Energy Density and Excellent Flexibility. ACS Applied Materials & Interfaces, 2017, 9, 9614-9619.	4.0	68
9	Atomic Layer Deposition of AlF₃ Using Trimethylaluminum and Hydrogen Fluoride. Journal of Physical Chemistry C, 2015, 119, 14185-14194.	1.5	67
10	Mechanism of Thermal Al₂O₃ Atomic Layer Etching Using Sequential Reactions with Sn(acac)₂ and HF. Chemistry of Materials, 2015, 27, 3648-3657.	3.2	59
11	Atomic Layer Deposition of Metal Fluorides Using HFâ€“Pyridine as the Fluorine Precursor. Chemistry of Materials, 2016, 28, 2022-2032.	3.2	54
12	Atomic Layer Deposition of LiOH and Li₂CO₃ Using Lithium t-Butoxide as the Lithium Source. ECS Transactions, 2010, 33, 223-229.	0.3	52
13	Molecular Layer Deposition of Aluminum Alkoxide Polymer Films Using Trimethylaluminum and Glycidol. Langmuir, 2011, 27, 15155-15164.	1.6	41
14	Thermal atomic layer etching of HfO2 using HF for fluorination and TiCl4 for ligand-exchange. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	40
15	Thermal Atomic Layer Etching of Al₂O₃, HfO₂, and ZrO₂ Using Sequential Hydrogen Fluoride and Dimethylaluminum Chloride Exposures. Journal of Physical Chemistry C, 2019, 123, 18455-18466.	1.5	40
16	Atomic Layer Etching of AlF₃ Using Sequential, Self-Limiting Thermal Reactions with Sn(acac)₂ and Hydrogen Fluoride. Journal of Physical Chemistry C, 2015, 119, 25385-25393.	1.5	34
17	Molecular Layer Deposition of Conductive Hybrid Organic-Inorganic Thin Films Using Diethylzinc and Hydroquinone. ECS Transactions, 2011, 33, 191-195.	0.3	33
18	In Situ Thermal Atomic Layer Etching for Sub-5 nm InGaAs Multigate MOSFETs. Nano Letters, 2019, 19, 5159-5166.	4.5	32

#	Article	IF	Citations
19	Cross-linked aluminum dioxybenzene coating for stabilization of silicon electrodes. Nano Energy, 2016, 22, 202-210.	8.2	30
20	First Transistor Demonstration of Thermal Atomic Layer Etching: InGaAs FinFETs with sub-5 nm Fin-width Featuring in situ ALE-ALD. , 2018, , .		24
21	Thermal Atomic Layer Etching of Gallium Oxide Using Sequential Exposures of HF and Various Metal Precursors. Chemistry of Materials, 2020, 32, 5937-5948.	3.2	20
22	Thermal etching of AlF3 and thermal atomic layer etching of Al2O3. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 022603.	0.9	20
23	Mitigating irreversible capacity losses from carbon agents via surface modification. Journal of Power Sources, 2015, 275, 605-611.	4.0	14